To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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# HM62W16258BI Series

4 M SRAM (256-kword × 16-bit)

ADE-203-1072A (Z)
Rev. 1.0
Jun. 10, 1999

## Description

The Hitachi HM62W16258BI Series is 4-Mbit static RAM organized 262,144-word × 16-bit. HM62W16258BI Series has realized higher density, higher performance and low power consumption by employing Hi-CMOS process technology. It offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It is packaged in standard 44-pin plastic TSOPII.

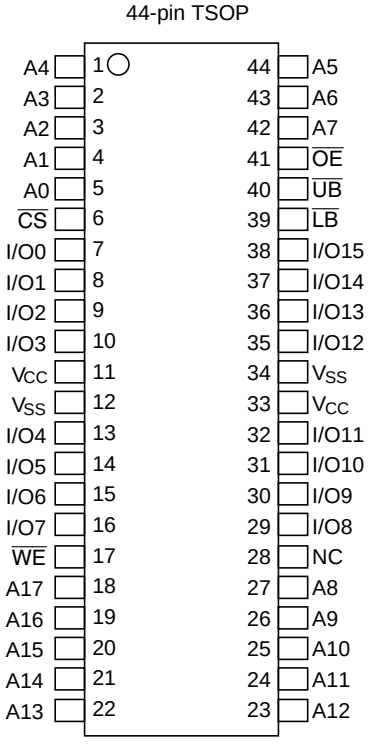
## Features

- Single 3.3 V supply: 3.3 V ± 0.3 V
- Fast access time: 70 ns (max)
- Power dissipation:
  - Active: 9.9 mW (typ)
  - Standby: 3.3 µW (typ)
- Completely static memory.
  - No clock or timing strobe required
- Equal access and cycle times
- Common data input and output.
  - Three state output
- Battery backup operation.
- Temperature range: –40 to 85°C

## Ordering Information

| Type No. | Access time | Package |
|---|---|---|
| HM62W16258BLTTI-7 | 70 ns | 400-mil 44-pin plastic TSOPII (normal-bend type) (TTP-44DB) |

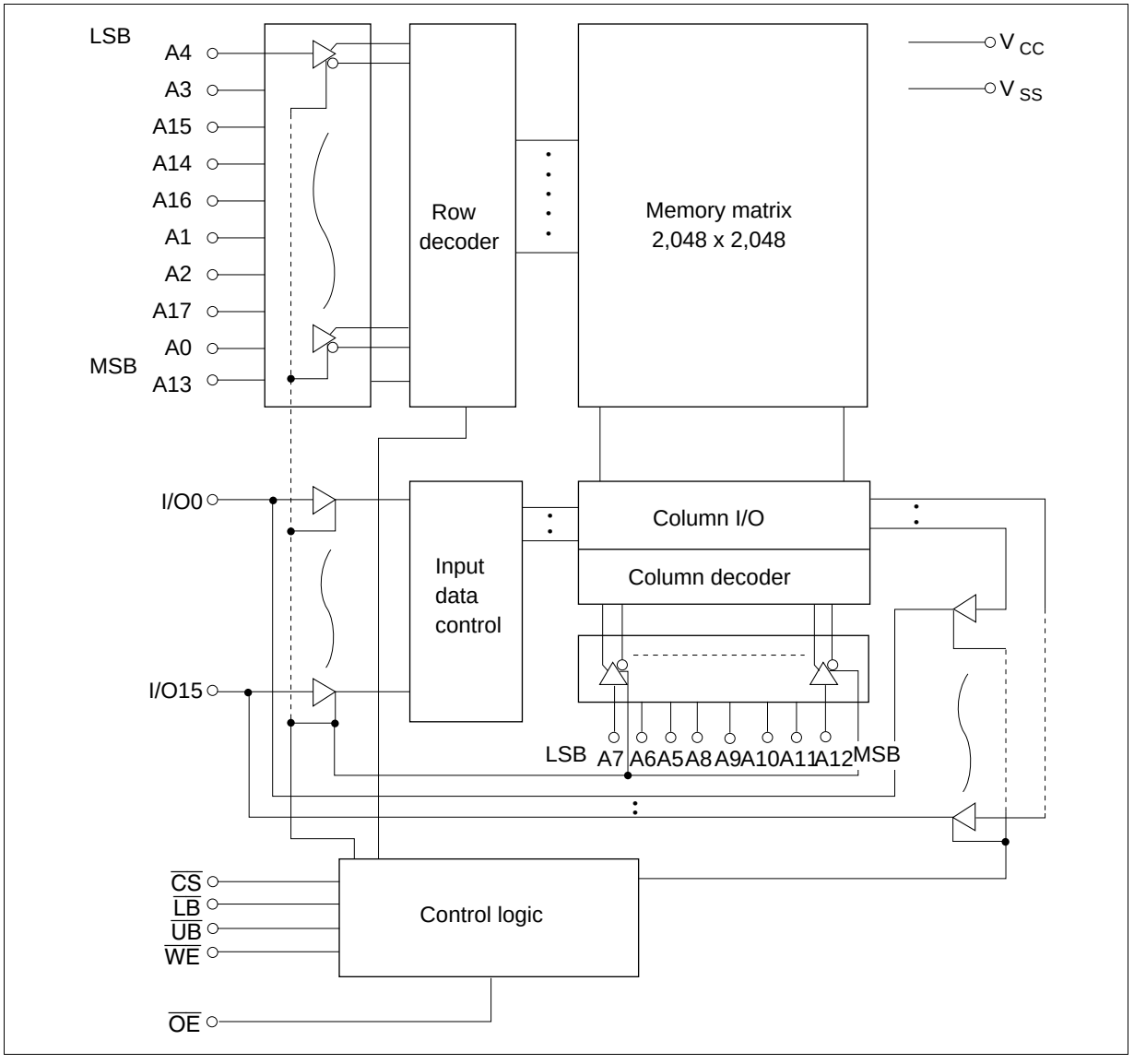
## Pin Arrangement




## Pin Description

| Pin name | Function |
|---|---|
| A0 to A17 | Address input |
| I/O0 to I/O15 | Data input/output |
| $\overline{CS}$ | Chip select |
| $\overline{WE}$ | Write enable |
| $\overline{OE}$ | Output enable |
| $\overline{LB}$ | Lower byte select |
| $\overline{UB}$ | Upper byte select |
| $V_{CC}$ | Power supply |
| $V_{SS}$ | Ground |
| NC | No connection |

## Block Diagram



## Operation Table

| $\overline{CS}$ | $\overline{WE}$ | $\overline{OE}$ | $\overline{UB}$ | $\overline{LB}$ | I/O0 to I/O7 | I/O8 to I/O15 | Operation |
|---|---|---|---|---|---|---|---|
| H | × | × | × | × | High-Z | High-Z | Standby |
| × | × | × | H | H | High-Z | High-Z | Standby |
| L | H | L | L | L | Dout | Dout | Read |
| L | H | L | H | L | Dout | High-Z | Lower byte read |
| L | H | L | L | H | High-Z | Dout | Upper byte read |
| L | L | × | L | L | Din | Din | write |
| L | L | × | H | L | Din | High-Z | Lower byte write |
| L | L | × | L | H | High-Z | Din | Upper byte write |
| L | H | H | × | × | High-Z | High-Z | Output disable |

Note: H: $V_{IH}$, L: $V_{IL}$, ×: $V_{IH}$ or $V_{IL}$

## Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Power supply voltage relative to $V_{SS}$ | $V_{CC}$ | –0.5 to + 4.6 | V |
| Terminal voltage on any pin relative to $V_{SS}$ | $V_T$ | –0.5*[1] to $V_{CC}$ + 0.3*[2] | V |
| Power dissipation | $P_T$ | 1.0 | W |
| Storage temperature range | Tstg | –55 to +125 | °C |
| Storage temperature range under bias | Tbias | –40 to +85 | °C |

Notes: 1. $V_T$ min: –3.0 V for pulse half-width ≤ 30 ns.
2. Maximum voltage is +4.6 V.

## DC Operating Conditions

| Parameter | Symbol | Min | Typ | Max | Unit | Note |
|---|---|---|---|---|---|---|
| Supply voltage | $V_{CC}$ | 3.0 | 3.3 | 3.6 | V | |
| | $V_{SS}$ | 0 | 0 | 0 | V | |
| Input high voltage | $V_{IH}$ | 2.2 | — | $V_{CC}$ + 0.3 | V | |
| Input low voltage | $V_{IL}$ | –0.3 | — | 0.6 | V | 1 |
| Ambient temperature range | Ta | –40 | — | 85 | °C | |

Note: 1. $V_{IL}$ min: –3.0 V for pulse half-width ≤ 30 ns.

## DC Characteristics

| Parameter | | Symbol | Min | Typ*[1] | Max | Unit | Test conditions |
|---|---|---|---|---|---|---|---|
| Input leakage current | | $\|I_{LI}\|$ | — | — | 1 | µA | Vin = $V_{SS}$ to $V_{CC}$ |
| Output leakage current | | $\|I_{LO}\|$ | — | — | 1 | µA | $\overline{CS}$ = $V_{IH}$ or $\overline{OE}$ = $V_{IH}$ or $\overline{WE}$ = $V_{IL}$, or $\overline{LB}$ = $\overline{UB}$ = $V_{IH}$, $V_{I/O}$ = $V_{SS}$ to $V_{CC}$ |
| Operating current | | $I_{CC}$ | — | — | 20 | mA | $\overline{CS}$ = $V_{IL}$, Others = $V_{IH}/V_{IL}$, $I_{I/O}$ = 0 mA |
| Average operating current | HM62W16258BI-7 | $I_{CC1}$ | — | — | 70 | mA | Min. cycle, duty = 100%, $I_{I/O}$ = 0 mA, $\overline{CS}$ = $V_{IL}$, Others = $V_{IH}/V_{IL}$ |
| | | $I_{CC2}$ | — | 3 | 15 | mA | Cycle time = 1 µs, duty = 100%, $I_{I/O}$ = 0 mA, $\overline{CS}$ ≤ 0.2 V, $V_{IH}$ ≥ $V_{CC}$ – 0.2 V, $V_{IL}$ ≤ 0.2 V |
| Standby current | | $I_{SB}$ | — | — | 0.3 | mA | $\overline{CS}$ = $V_{IH}$ |
| Standby current | | $I_{SB1}$ | — | 1 | 40 | µA | 0 V ≤ Vin ≤ $\overline{CS}$ ≥ $V_{CC}$ – 0.2 V |
| Output high voltage | | $V_{OH}$ | 2.4 | — | — | V | $I_{OH}$ = –1 mA |
| | | | $V_{CC}$ – 0.2 | — | — | V | $I_{OH}$ = –100 µA |
| Output low voltage | | $V_{OL}$ | — | — | 0.4 | V | $I_{OL}$ = 2 mA |
| | | | — | — | 0.2 | V | $I_{OL}$ = 100 µA |

Notes: 1. Typical values are at $V_{CC}$ = 3.0 V, Ta = +25°C and not guaranteed.

## Capacitance (Ta = +25°C, f = 1.0 MHz)

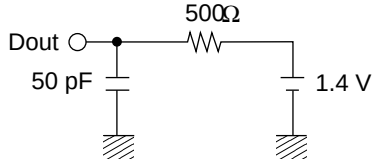
| Parameter | Symbol | Min | Typ | Max | Unit | Test conditions | Note |
|---|---|---|---|---|---|---|---|
| Input capacitance | Cin | — | — | 8 | pF | Vin = 0 V | 1 |
| Input/output capacitance | $C_{I/O}$ | — | — | 10 | pF | $V_{I/O}$ = 0 V | 1 |

Note: 1. This parameter is sampled and not 100% tested.

## AC Characteristics (Ta = –40 to +85°C, $V_{CC}$ = 3.3 V ± 0.3 V, unless otherwise noted.)

### Test Conditions

- Input pulse levels: $V_{IL}$ = 0.4 V, $V_{IH}$ = 2.4 V
- Input rise and fall time: 5 ns
- Input timing reference levels: 1.4 V
- Output timing reference levels: 1.4 V
- Output load (Including scope and jig)




### Read Cycle

| | | HM62W16258BI | | | |
|---|---|---|---|---|---|
| | | -7 | | | |
| **Parameter** | **Symbol** | **Min** | **Max** | **Unit** | **Notes** |
| Read cycle time | $t_{RC}$ | 70 | — | ns | |
| Address access time | $t_{AA}$ | — | 70 | ns | |
| Chip select access time | $t_{ACS}$ | — | 70 | ns | |
| Output enable to output valid | $t_{OE}$ | — | 40 | ns | |
| Output hold from address change | $t_{OH}$ | 10 | — | ns | |
| $\overline{LB}$, $\overline{UB}$ access time | $t_{BA}$ | — | 70 | ns | |
| Chip select to output in low-Z | $t_{CLZ}$ | 10 | — | ns | 2, 3 |
| $\overline{LB}$, $\overline{UB}$ enable to low-z | $t_{BLZ}$ | 5 | — | ns | 2, 3 |
| Output enable to output in low-Z | $t_{OLZ}$ | 5 | — | ns | 2, 3 |
| Chip deselect to output in high-Z | $t_{CHZ}$ | 0 | 25 | ns | 1, 2, 3 |
| $\overline{LB}$, $\overline{UB}$ disable to high-Z | $t_{BHZ}$ | 0 | 25 | ns | 1, 2, 3 |
| Output disable to output in high-Z | $t_{OHZ}$ | 0 | 25 | ns | 1, 2, 3 |

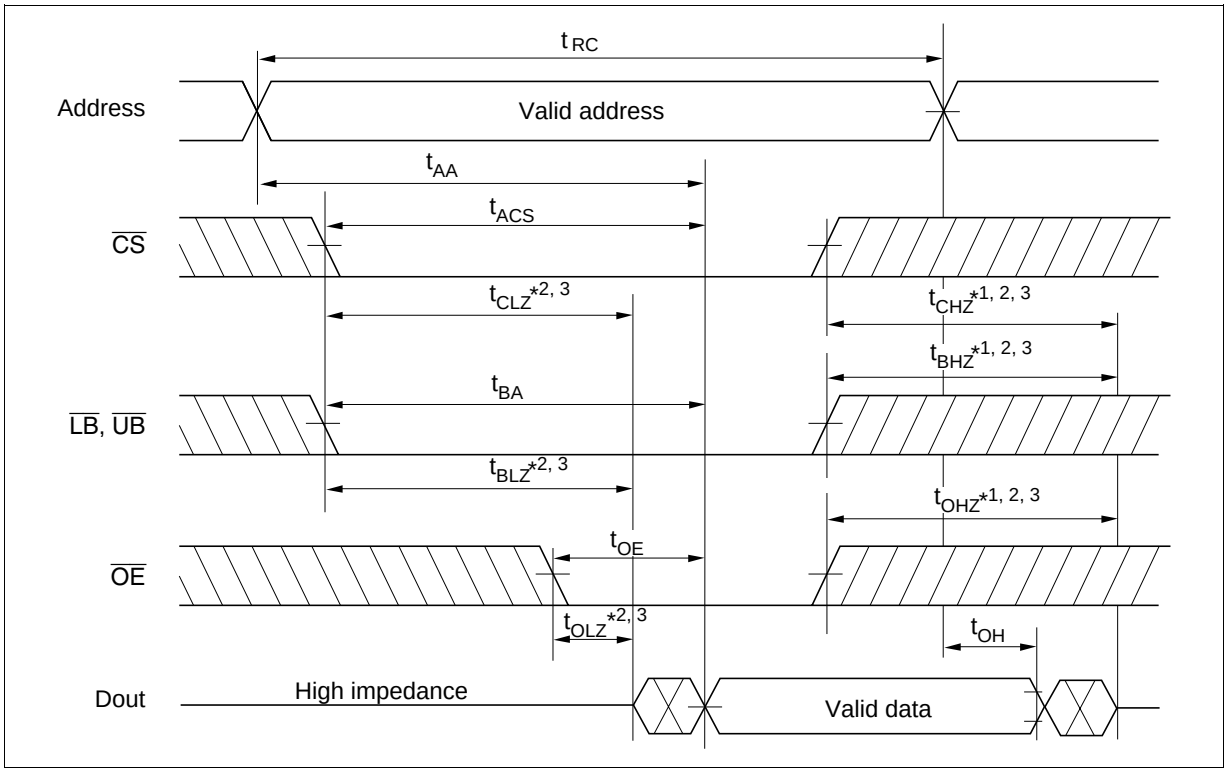
### Write Cycle

| | | HM62W16258BI | | | |
|---|---|---|---|---|---|
| | | -7 | | | |
| **Parameter** | **Symbol** | **Min** | **Max** | **Unit** | **Notes** |
| Write cycle time | $t_{WC}$ | 70 | — | ns | |
| Address valid to end of write | $t_{AW}$ | 60 | — | ns | |
| Chip selection to end of write | $t_{CW}$ | 60 | — | ns | 5 |
| Write pulse width | $t_{WP}$ | 50 | — | ns | 4 |
| $\overline{LB}$, $\overline{UB}$ valid to end of write | $t_{BW}$ | 55 | — | ns | |
| Address setup time | $t_{AS}$ | 0 | — | ns | 6 |
| Write recovery time | $t_{WR}$ | 0 | — | ns | 7 |
| Data to write time overlap | $t_{DW}$ | 30 | — | ns | |
| Data hold from write time | $t_{DH}$ | 0 | — | ns | |
| Output active from end of write | $t_{OW}$ | 5 | — | ns | 2 |
| Output disable to output in High-Z | $t_{OHZ}$ | 0 | 25 | ns | 1, 2 |
| Write to output in high-Z | $t_{WHZ}$ | 0 | 25 | ns | 1, 2 |

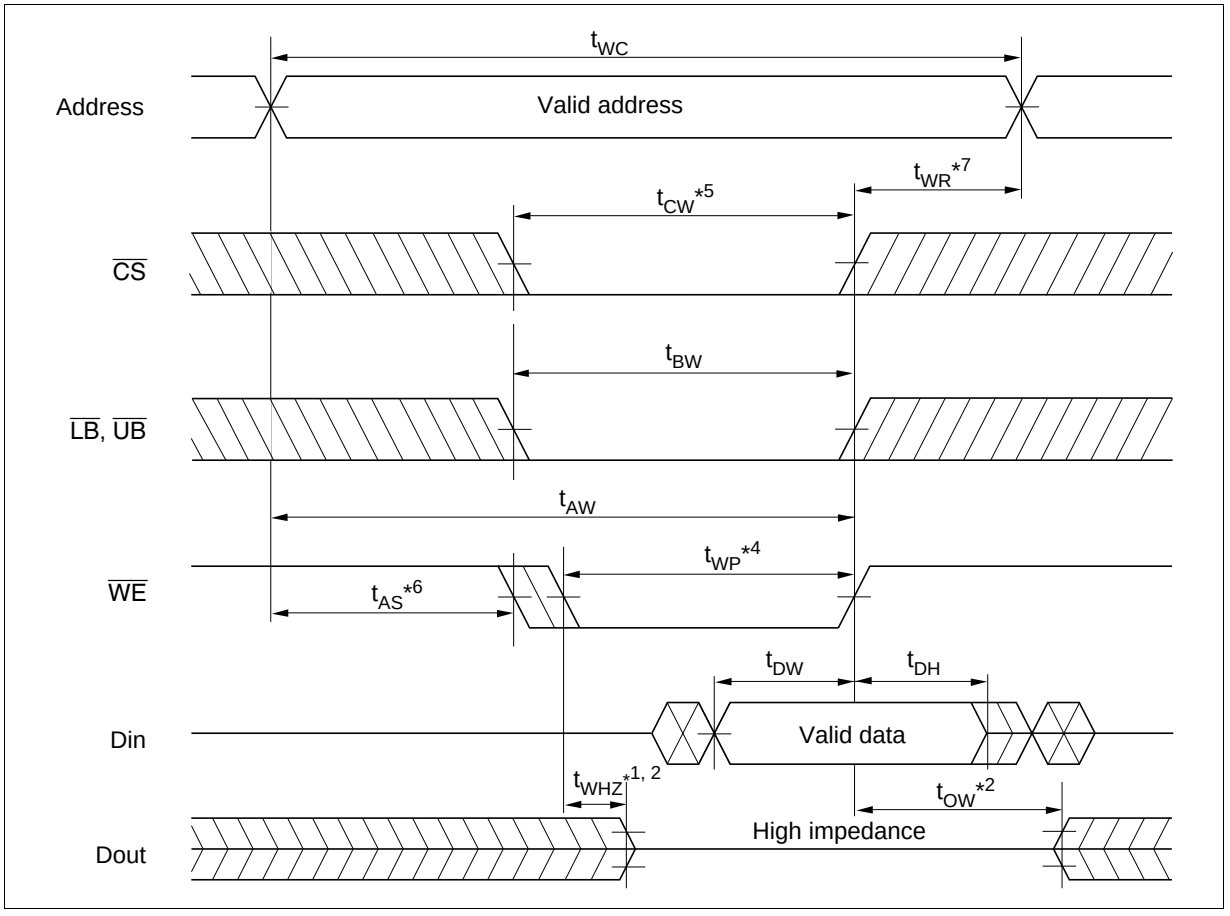
Notes:
1. $t_{CHZ}$, $t_{OHZ}$, $t_{WHZ}$ and $t_{BHZ}$ are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
2. This parameter is sampled and not 100% tested.
3. At any given temperature and voltage condition, $t_{HZ}$ max is less than $t_{LZ}$ min both for a given device and from device to device.
4. A write occures during the overlap of a low $\overline{CS}$, a low $\overline{WE}$ and a low $\overline{LB}$ or a low $\overline{UB}$. A write begins at the latest transition among $\overline{CS}$ going low, $\overline{WE}$ going low and $\overline{LB}$ going low or $\overline{UB}$ going low. A write ends at the earliest transition among $\overline{CS}$ going high, $\overline{WE}$ going high and $\overline{LB}$ going high or $\overline{UB}$ going high. $t_{WP}$ is measured from the beginning of write to the end of write.
5. $t_{CW}$ is measured from the later of $\overline{CS}$ going low to the end of write.
6. $t_{AS}$ is measured from the address valid to the beginning of write.
7. $t_{WR}$ is measured from the earliest of $\overline{CS}$ or $\overline{WE}$ going high to the end of write cycle.

## Timing Waveform

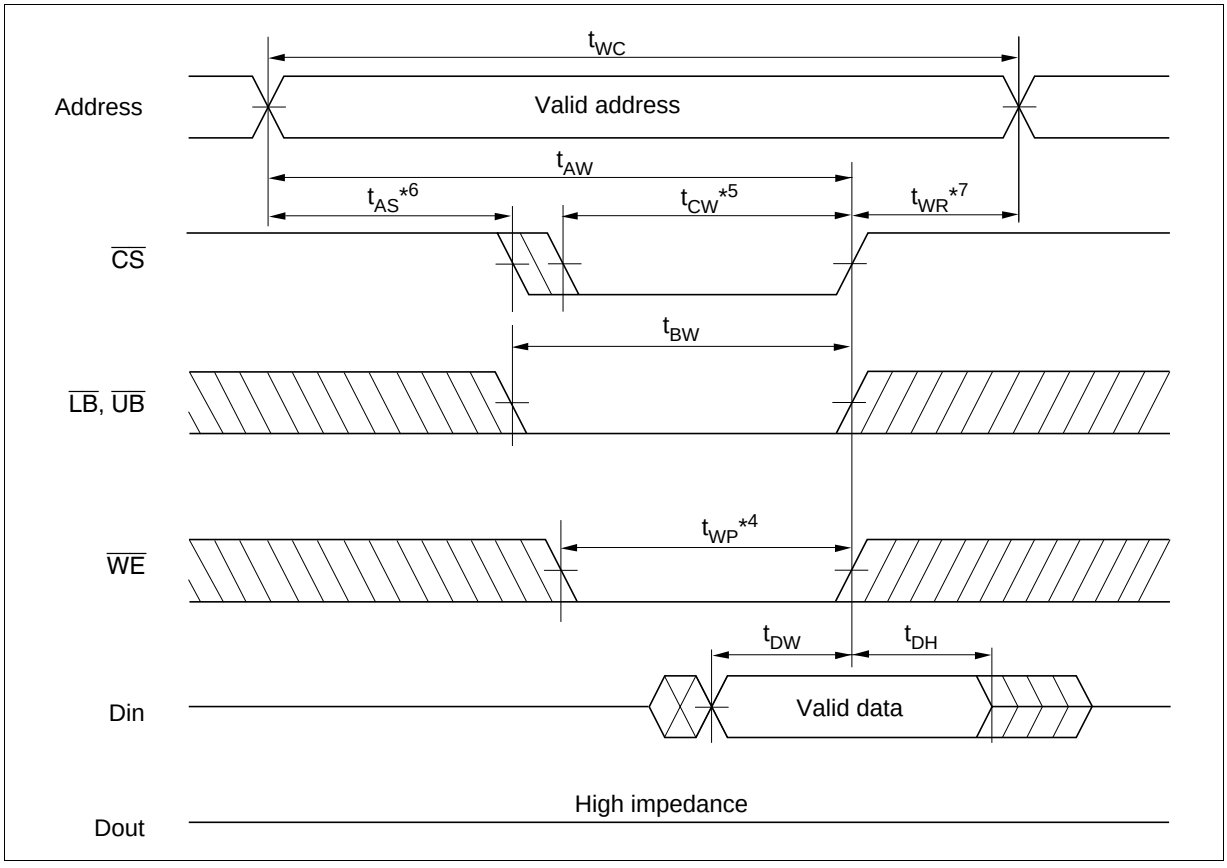
### Read Cycle



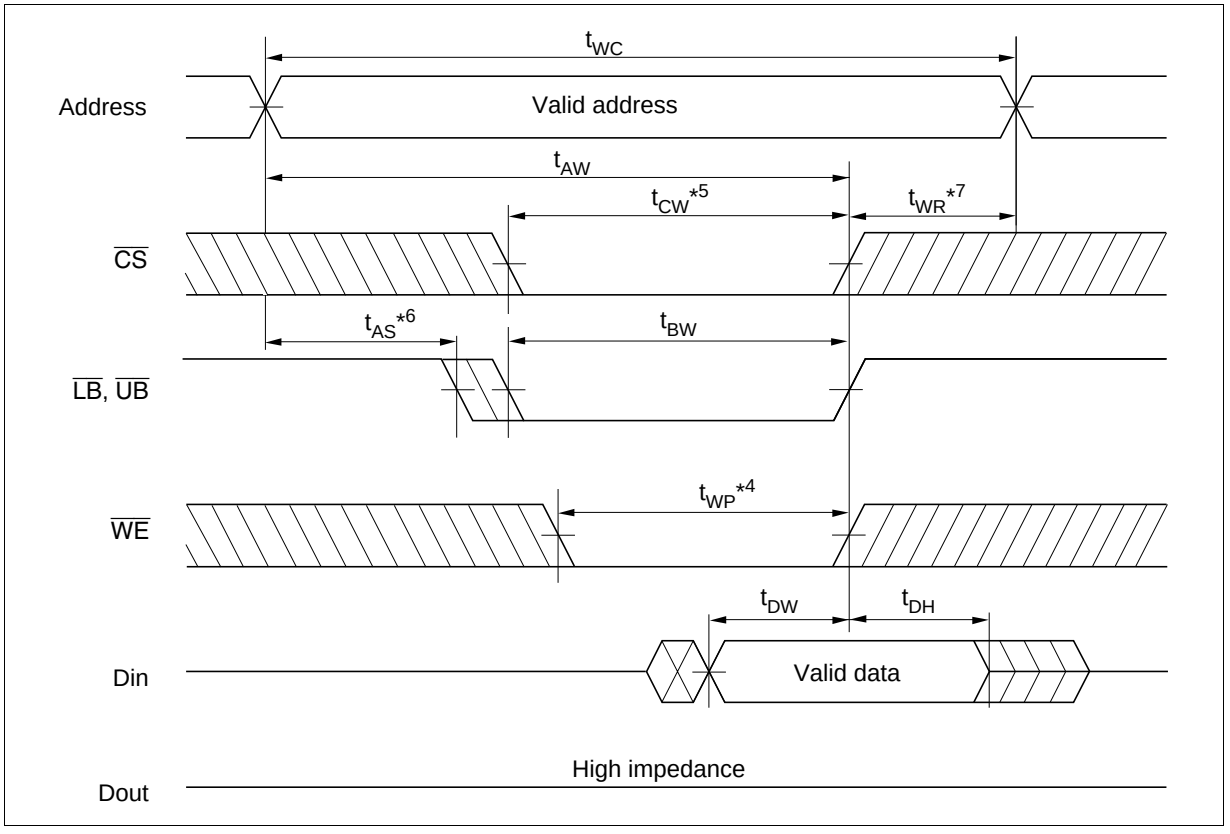
**Write Cycle (1)** ($\overline{WE}$ Clock)



**Write Cycle (2)** ($\overline{CS}$ Clock, $\overline{OE}$ = $V_{IH}$)



**Write Cycle (3)** ($\overline{LB}$, $\overline{UB}$ Clock, $\overline{OE}$ = $V_{IH}$)



## Low $V_{CC}$ Data Retention Characteristics (Ta = –40 to +85°C)

| Parameter | Symbol | Min | Typ*3 | Max | Unit | Test conditions*2 |
|---|---|---|---|---|---|---|
| $V_{CC}$ for data retention | $V_{DR}$ | 2.0 | — | — | V | Vin ≥ 0V<br>(1) $\overline{CS} \geq V_{CC} - 0.2$ V or<br>(2) $\overline{LB} = \overline{UB} \geq V_{CC} - 0.2$ V<br>$\overline{CS} \leq 0.2$ V |
| Data retention current | $I_{CCDR}$*1 | — | 0.8 | 20 | µA | $V_{CC}$ = 3.0 V, Vin ≥ 0V<br>(1) $\overline{CS} \geq V_{CC} - 0.2$ V or<br>(2) $\overline{LB} = \overline{UB} \geq V_{CC} - 0.2$ V<br>$\overline{CS} \leq 0.2$ V |
| Chip deselect to data retention time | $t_{CDR}$ | 0 | — | — | ns | See retention waveform |
| Operation recovery time | $t_R$ | $t_{RC}$*4 | — | — | ns | |

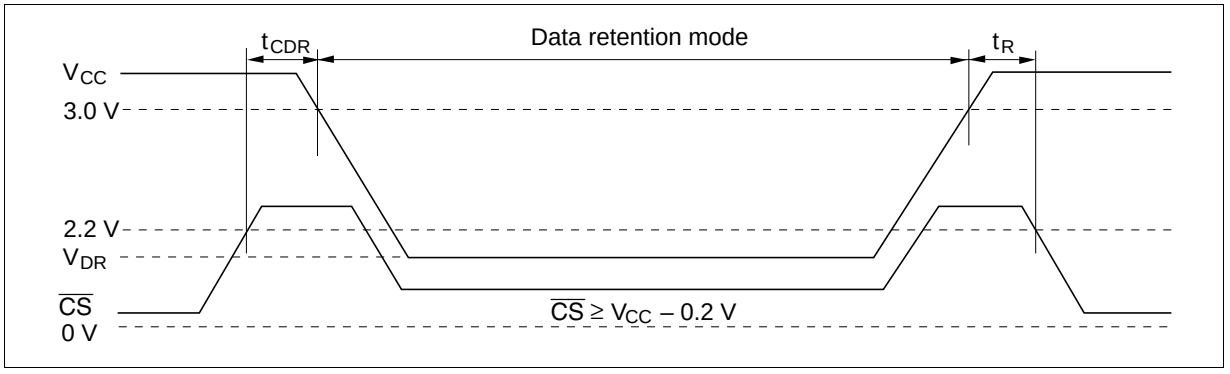
Notes: 1. 10 µA max. at Ta = 0 to +40°C.

2. $\overline{CS}$ controls address buffer, $\overline{WE}$ buffer, $\overline{OE}$ buffer, $\overline{LB}$, $\overline{UB}$ buffer and Din buffer. If $\overline{CS}$ controls data retention mode, Vin levels (address, $\overline{WE}$, $\overline{OE}$, $\overline{LB}$, $\overline{UB}$, I/O) can be in the high impedance state. If $\overline{LB}$, $\overline{UB}$ controls data retention mode, $\overline{LB}$, $\overline{UB}$ must be $\overline{LB} = \overline{UB} \geq V_{CC} - 0.2$ V, $\overline{CS}$ must be $\overline{CS} \leq 0.2$ V. The other input levels (address, $\overline{WE}$, $\overline{OE}$, I/O) can be in the high impedance state.

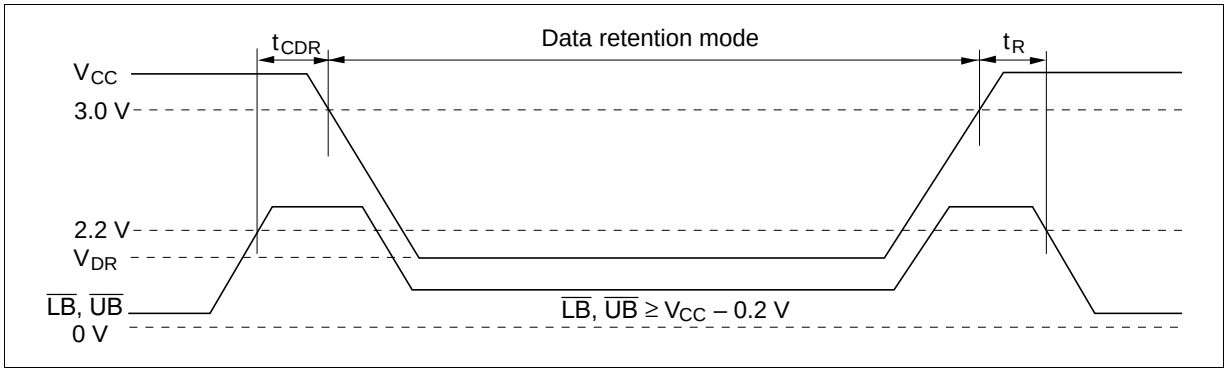
3. Typical values are at $V_{CC}$ = 3.0 V, Ta = +25˚C and not guaranteed.

4. $t_{RC}$ = read cycle time.

**Low $V_{CC}$ Data Retention Timing Waveform (1)** ($\overline{CS}$ Controlled)



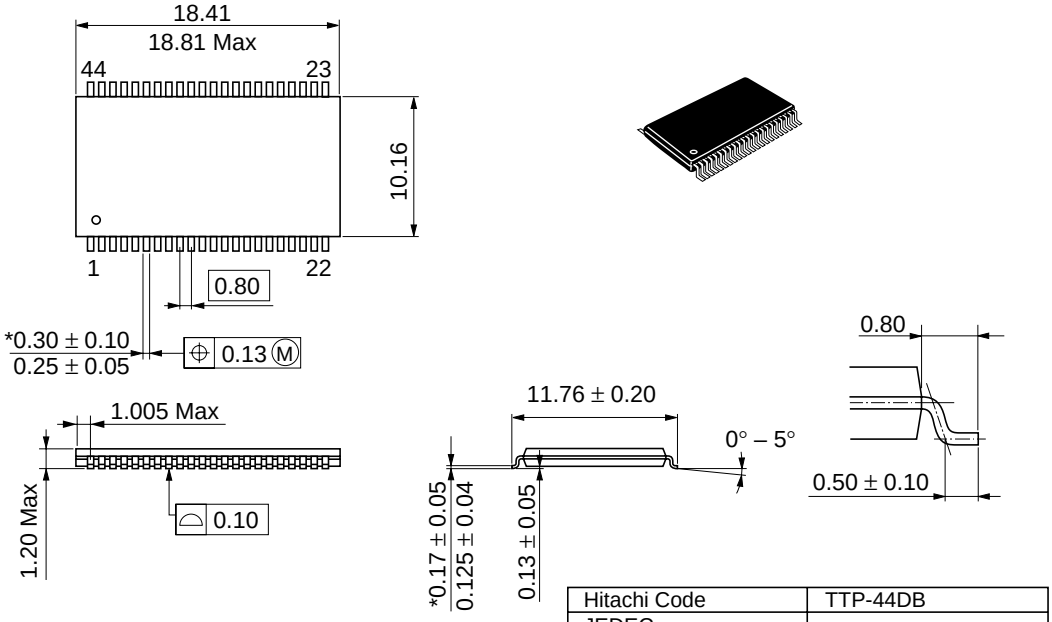

**Low $V_{CC}$ Data Retention Timing Waveform (2)** ($\overline{LB}$, $\overline{UB}$ Controlled)



## Package Dimensions

**HM62W16258BLTTI Series** (TTP-44DB)

Unit: mm




*Dimension including the plating thickness
Base material dimension

| | |
|---|---|
| Hitachi Code | TTP-44DB |
| JEDEC | — |
| EIAJ | — |
| Weight (reference value) | 0.43 g |

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